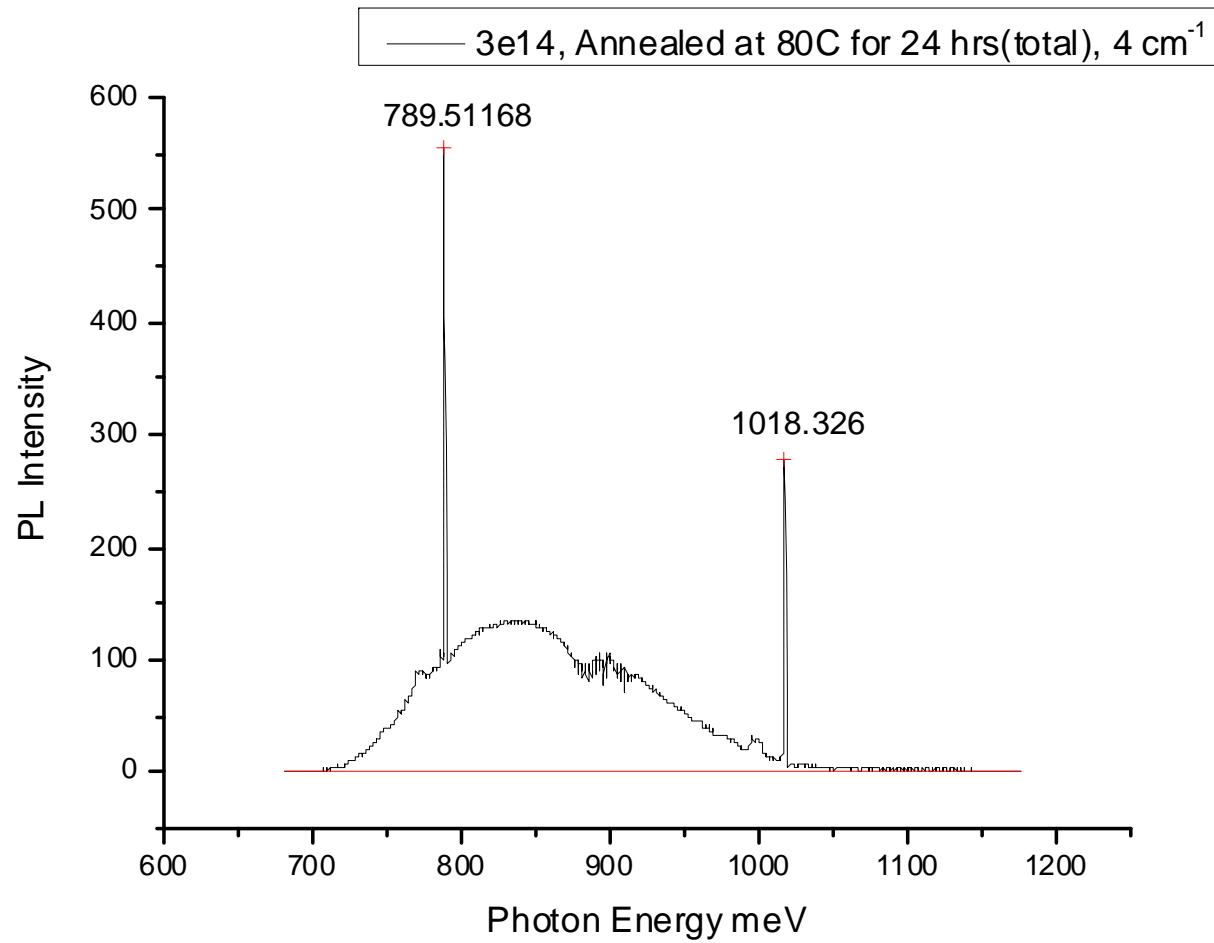


Photoluminescence characterisation of the WODEAN samples

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Technical details

- Magnetic Cz samples, irradiated with $1e12$ to $3e16$ cm^{-2} fast neutrons.
- Photoluminescence spectra measured at ~ 4 K, in liquid helium.
- Interest is in annealing at 80 C (accelerated room temperature annealing).



Example: 789 meV = C_iO_i, 1018 meV = W (3I ?)

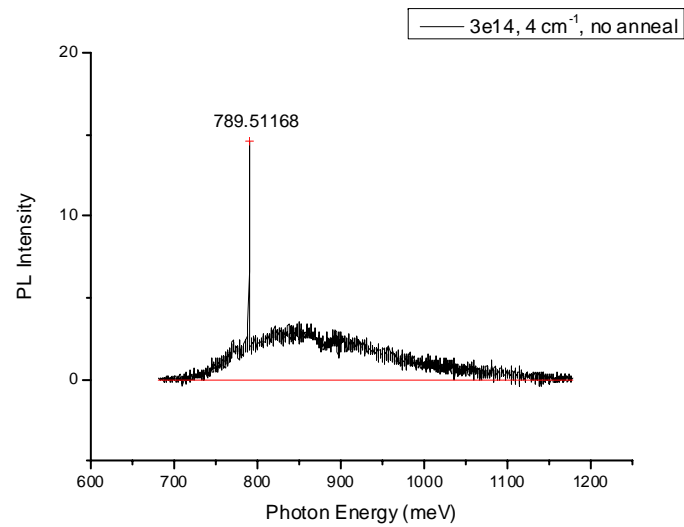
Photoluminescence

- High energy resolution : unique defect characterisation for sharp lines...
- ...but broad band PL is not identified.
- PL must be seen...
- ...defects may be non-radiative (VV) or PL quenched by other defects.

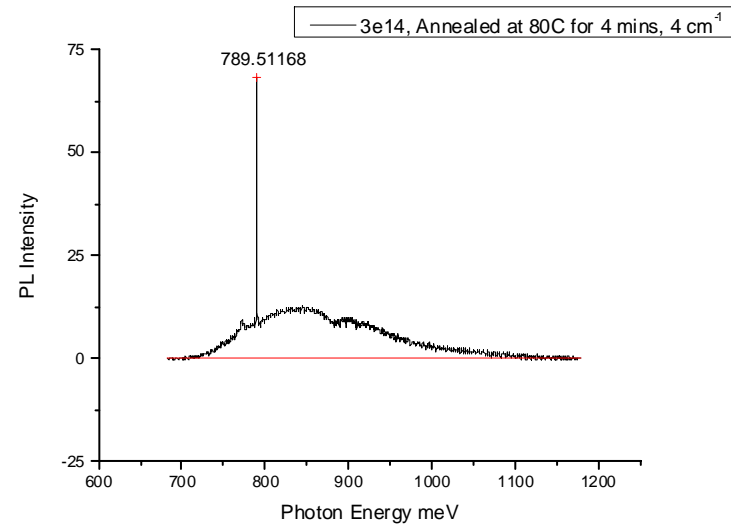
Annealing data

- 7 different fluences ($1e12$ to $3e16$ cm^{-2})
- Spectra as received and 4 anneals at 80 C and one at 450 C
- 42 spectra
- Sample spectra only here

Recovery at 80 C (4 mins)



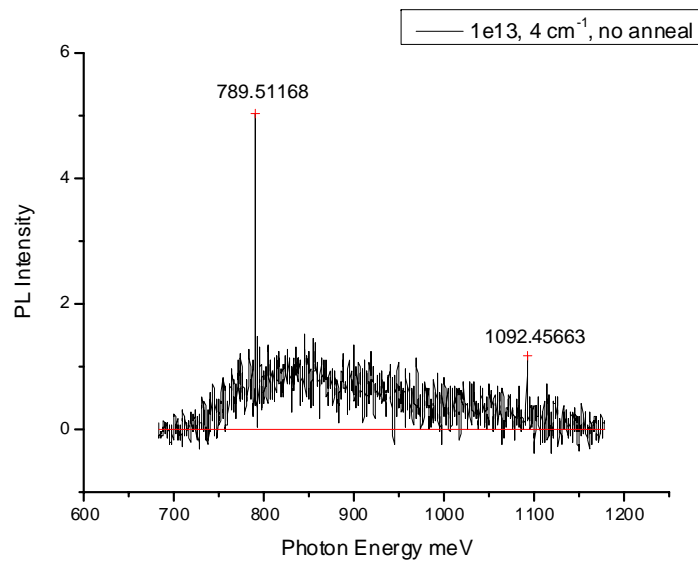
3e14 cm⁻² no anneal



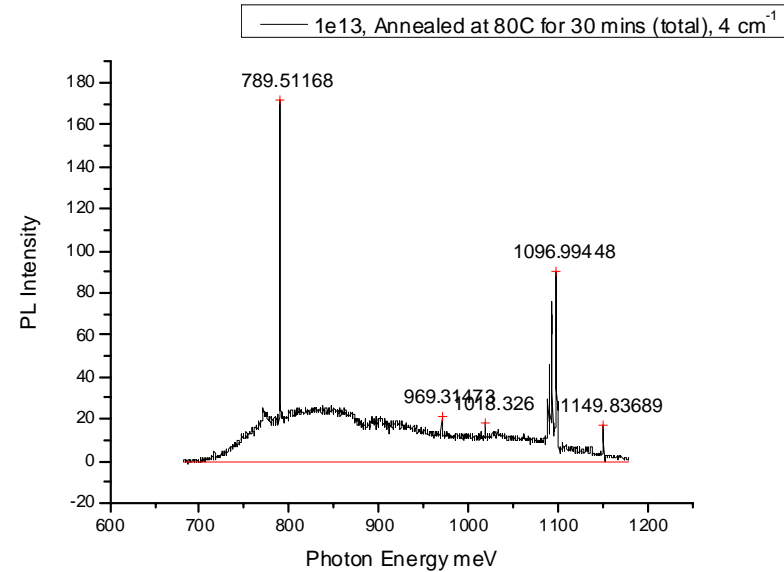
3e14 cm⁻² annealed 4 mins

All samples : No change in spectral shape

Recovery at 80 C (30 mins)



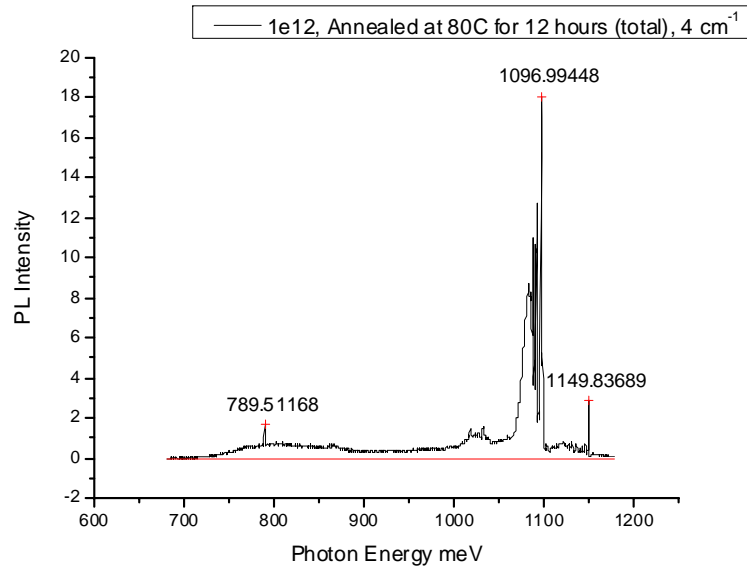
1e14 cm⁻² no anneal



1e14 cm⁻² annealed 30 mins

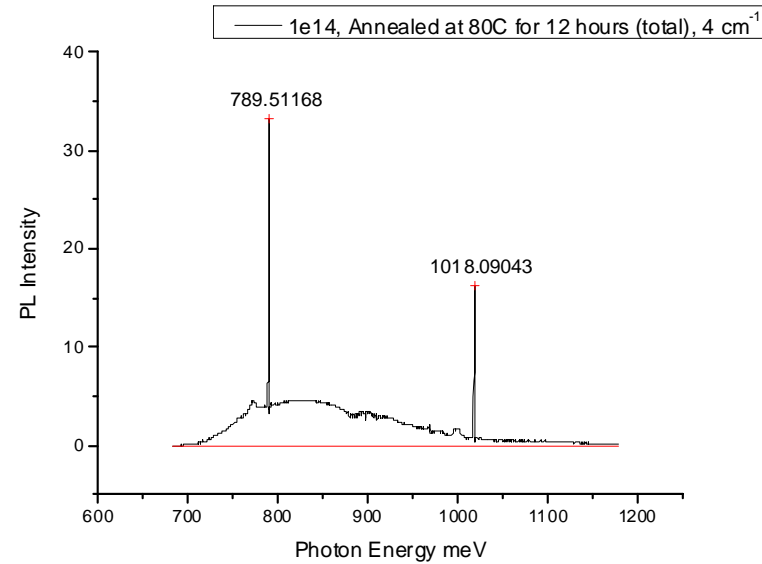
Lower fluences : Recovery of shallow PL, observation of C_iC_s and W (3 I's)

Recovery at 80 C (12 hrs)



1e12 cm⁻² annealed 12 hrs

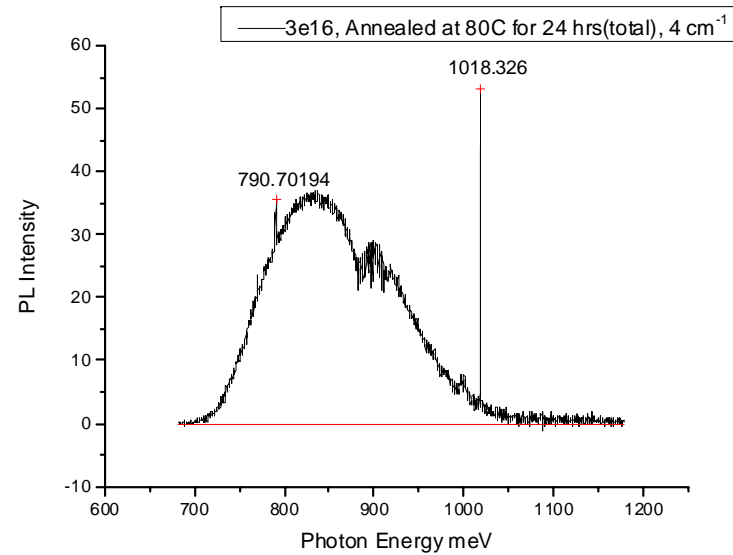
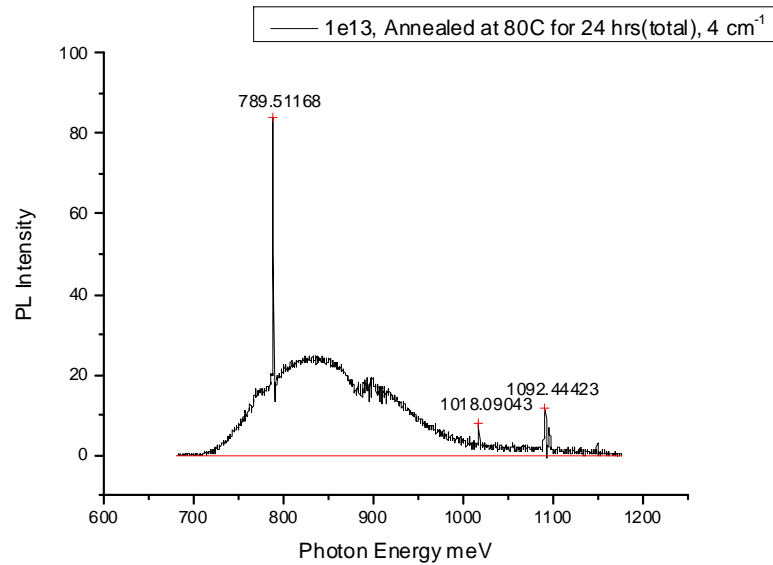
Lowest dose: almost complete recovery.



1e14 cm⁻² annealed 12 hrs

Higher fluences: C_iO_i and W but 1e16, 3e16 no change

Recovery at 80 C (24 hrs)



1e13 cm⁻² annealed 24 hrs

3e16 cm⁻² annealed 24 hrs

C_iC_s and W , with ratio of PL from W to C_iO_i increasing with fluence especially at the highest doses.

Summary of annealing

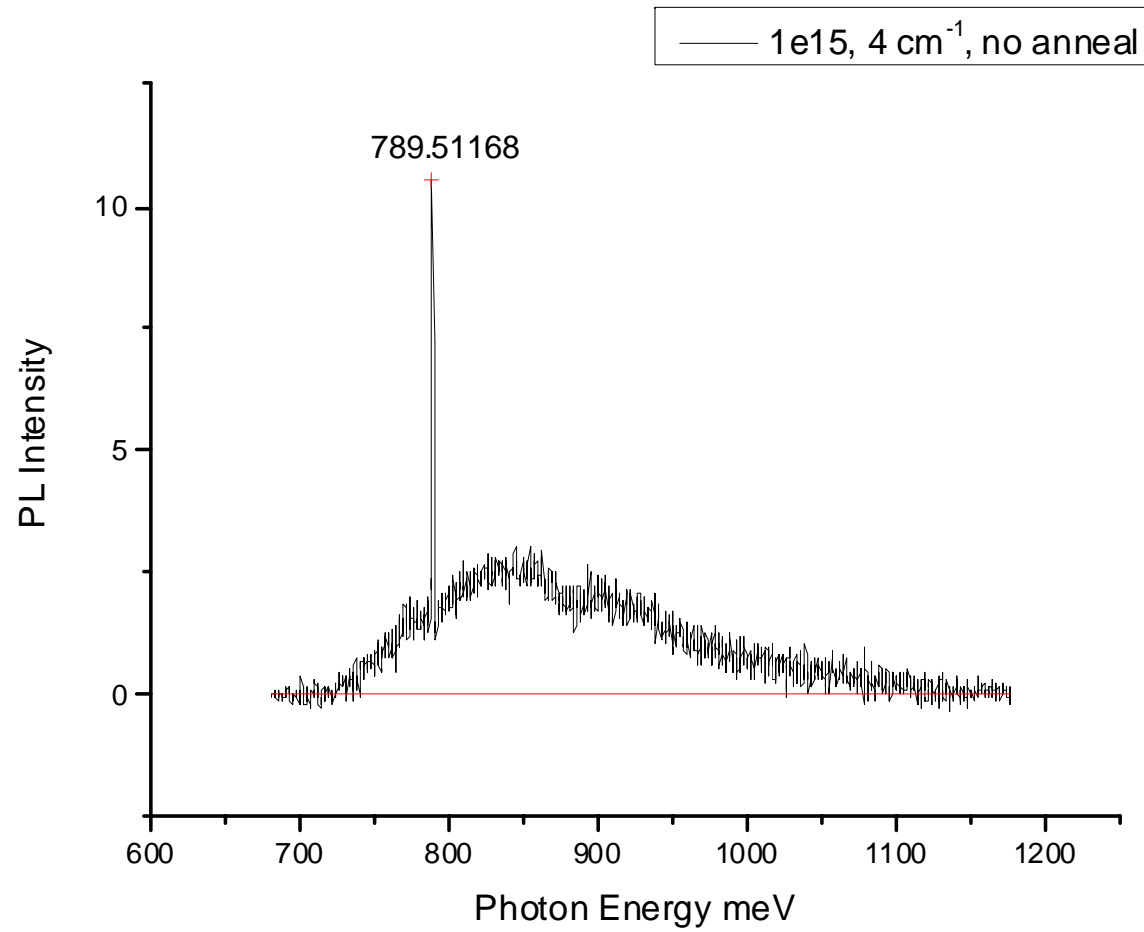
- As received: low PL intensity, C_iO_i plus broad band
- At 80 C, no change in bandshapes after 4 mins.
- After 30 mins, start of observing weak C_iC_s and W ; W continues to increase after 12 hrs and 24 hrs.

Radiation damage and C

- $C_s + I \rightarrow C_i$
- Thermal diffusion of C_i is
- $D = 0.44 \exp(-870 \text{ meV}/kT) \text{ cm}^2 \text{ s}^{-1}$, so
- $C_i + O_i \rightarrow C_iO_i$

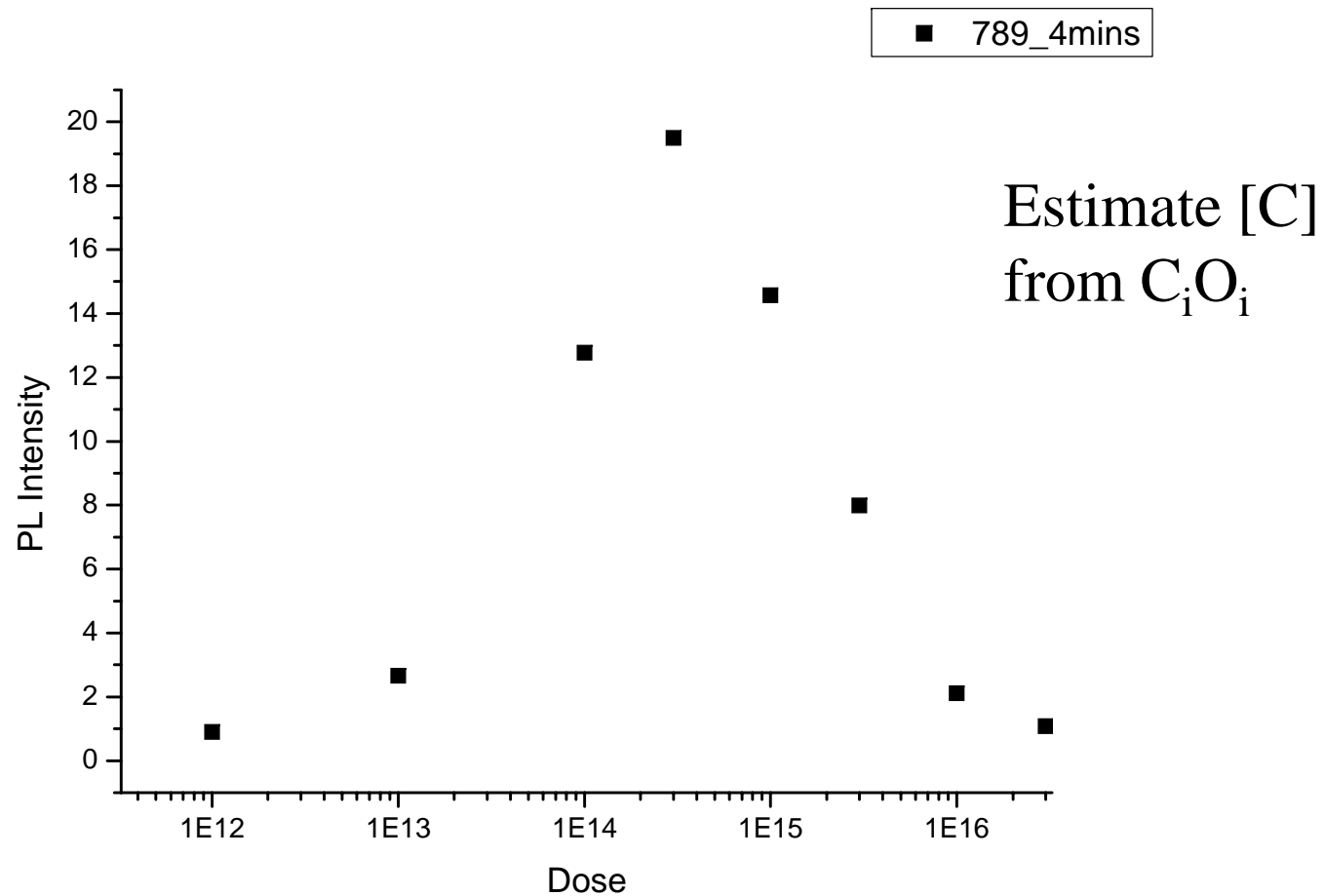
Carbon interstitials C_i : PL at 856 meV: Not seen

C_iO_i : PL at 789 meV : observed :



Carbon content

- $[C] < 2.5e15 \text{ cm}^{-3}$ from SIMS.
- At larger radiation fluences, $> 3e15 \text{ cm}^{-2}$, the concentration of generated I's exceeds $[C]$
- $C_s + I \rightarrow C_i$ $C_i + O_i \rightarrow C_iO_i$
- $C_iO_i + I \rightarrow IC_iO_i$ (Destruction of C_iO_i)

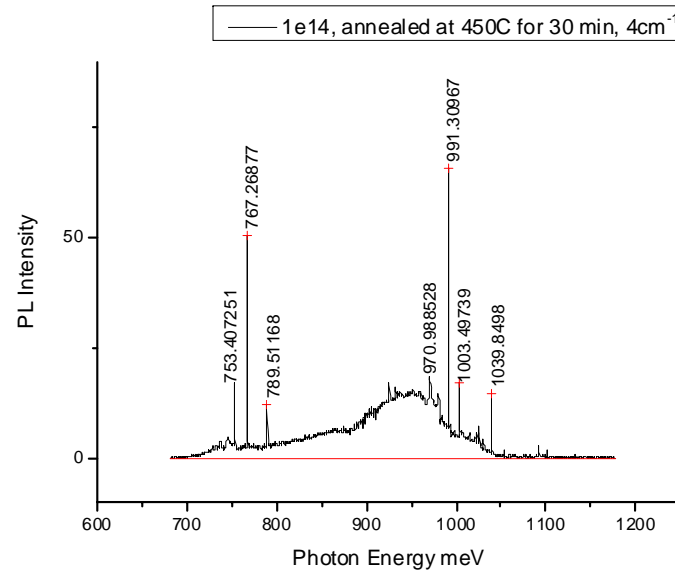


For 2 MeV electrons, peak 789 meV is when creation of I's is 0.75 [C]. For a production rate of $R = 0.7 \text{ cm}^{-1}$, peak at (5 to 6) $\text{e}14 \text{ cm}^{-2}$ implies $[C] \sim 5\text{e}14 \text{ cm}^{-3}$.

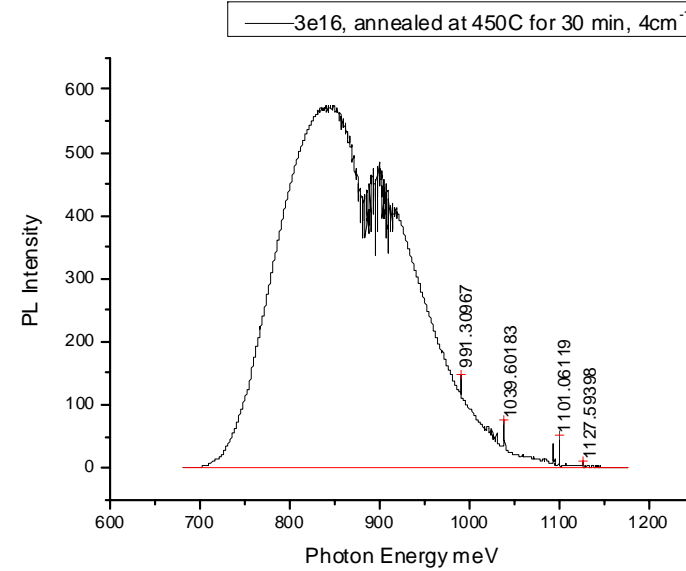
Summary / Next steps

- PL allows monitoring of annealing at 80 C.
- In principle estimate of carbon concentration : $[C] \sim 5 \times 10^{14} \text{ cm}^{-3}$?
- Next:
- Careful annealing in 20 to 80 C range, to give kinetics of W (3 I's?) defect.

Anneal at 450 C (30 mins)



1e14 cm⁻² and below: broad band gone

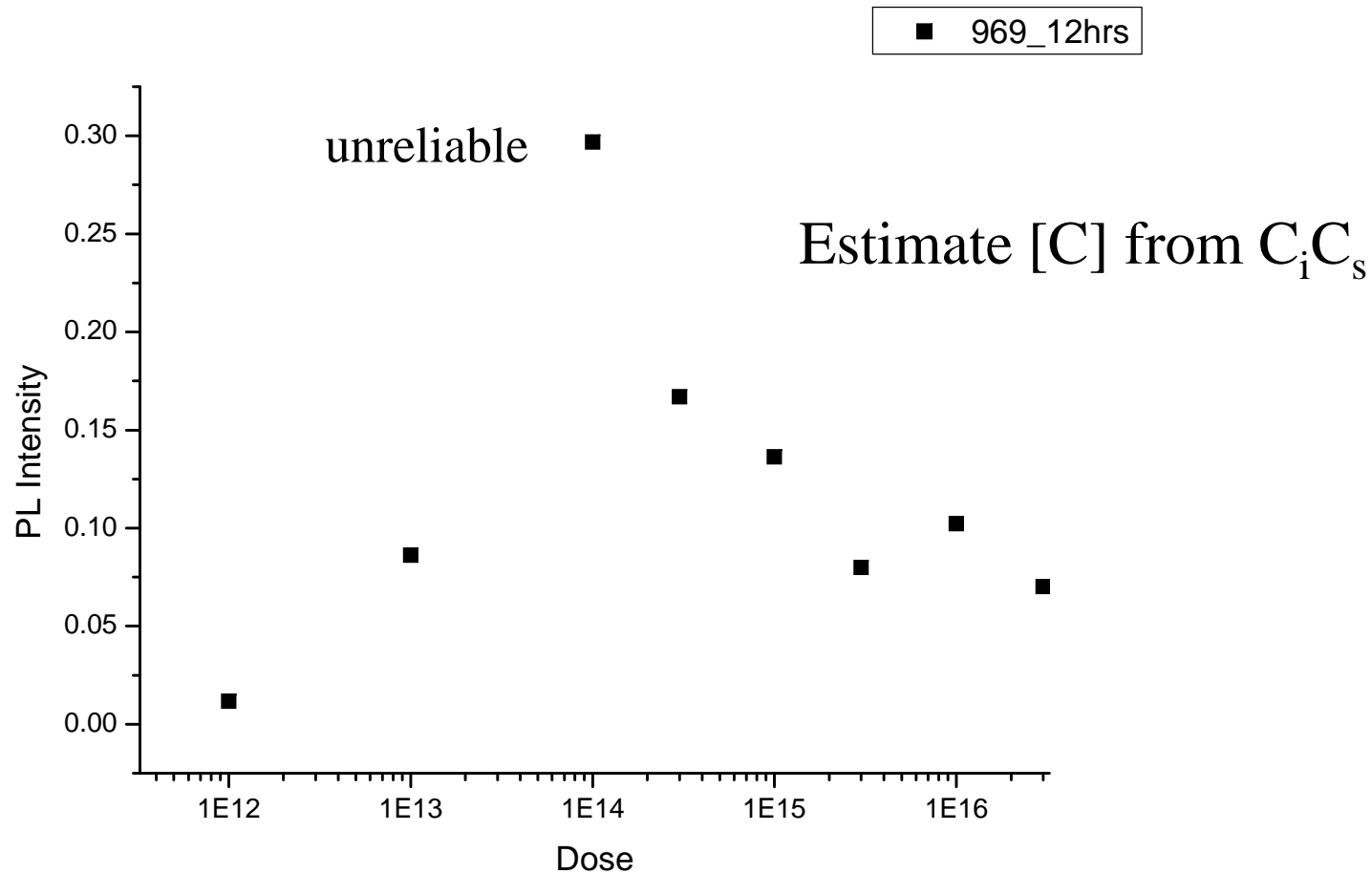


3e14 cm⁻² and above: broad band persists at increasing expense of sharp lines.

Shown is 3e16 cm⁻²

Problems: 1. Quenching

- From ion-implantation *at nominal RT*, PL is quenched when the mean distance between VVs is less than ~ 50 atoms.
- Assume production rate for VV of 1.3 cm^{-1} .
- At maximum fluence, $3 \times 10^{16} \text{ cm}^{-2}$, the mean VV separation is 110 atoms.
- Implies quenching is not important.



For 2 MeV electrons, peak 969 meV with $[C] \ll [O]$ is when creation of I's is $\sim 0.25 [C]$. For a production rate of $R = 0.7 \text{ cm}^{-1}$, peak at $2e14 \text{ cm}^{-2}$ implies $[C] = 6e14 \text{ cm}^{-3}$.